

#2 Pre Amdt A  
9-14-00  
R. Stokes

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : David L. Chapek  
Title : METHOD FOR CONTROLLING THE MORPHOLOGY OF  
DEPOSITED SILICON ON A SILICON DIOXIDE SUBSTRATE  
AND SEMICONDUCTOR DEVICES INCORPORATING SUCH  
DEPOSITED SILICON

Docket No. : MIO 0037 VA

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

Please preliminarily amend the above-identified application as follows.

IN THE TITLE

a' Please delete the title and insert the following new title: ~~SEMICONDUCTOR~~  
DEVICES INCLUDING A LAYER OF POLYCRYSTALLINE SILICON HAVING A SMOOTH  
MORPHOLOGY~.

IN THE SPECIFICATION

a<sup>2</sup> At page 1 after the Title, please insert the following:

~CROSS REFERENCE TO RELATED APPLICATIONS

This application is a division of U.S. Patent Application Serial No. 09/072,262, filed  
May 4, 1998.~

IN THE CLAIMS

Please cancel claims 1-8, and 13.

Please amend claims 9-12 and 14 to read as follows:

- a<sup>3</sup> 9. A semiconductor device precursor comprising:
- a semiconductor substrate;
  - a layer of silicon dioxide formed on said semiconductor substrate, said layer of silicon dioxide having been doped with hydrogen ions deposited by a plasma source ion implantation process [to provide a layer of polycrystalline silicon, which is subsequently deposited on said layer of silicon dioxide with a smooth morphology]; and
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